# PDTC123Y series

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ Rev. 04 — 16 November 2009 Product data sh

Product data sheet

## **Product profile**

## 1.1 General description

NPN Resistor-Equipped Transistors (RET) family.

Table 1. **Product overview** 

Type number	Package	Package			
	NXP	JEITA	JEDEC		
PDTC123YE	SOT416	SC-75	-	PDTA123YE	
PDTC123YK	SOT346	SC-59A	TO-236	PDTA123YK	
PDTC123YM	SOT883	SC-101	-	PDTA123YM	
PDTC123YS[1]	SOT54	SC-43A	TO-92	PDTA123YS	
PDTC123YT	SOT23	-	TO-236AB	PDTA123YT	
PDTC123YU	SOT323	SC-70	-	PDTA123YU	

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2).

## 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

## 1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

### Circuit drivers

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	

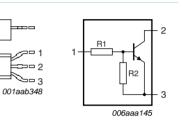


# 2. Pinning information

Table 3. Pinning

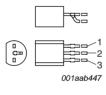
Pin	Description	Simplified outline Symbol
SOT54		
1	input (base)	
2	output (collector)	2
3	GND (emitter)	001aab347 R1 R2

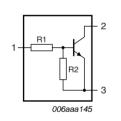
1	input (base)
2	output (collector)
3	GND (emitter)



### **SOT54** variant

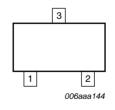
1	input (base)
2	output (collector)
3	GND (emitter)

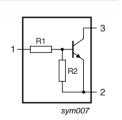




## SOT23; SOT323; SOT346; SOT416

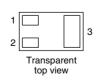
1	input (base)
2	GND (emitter)
3	output (collector)

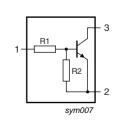




### **SOT883**

1	input (base)
2	GND (emitter)
3	output (collector)





2 of 11

## 3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTC123YE	SC-75	plastic surface mounted package; 3 leads	SOT416			
PDTC123YK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTC123YM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOT883			
PDTC123YS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTC123YT	-	plastic surface mounted package; 3 leads	SOT23			
PDTC123YU	SC-70	plastic surface mounted package; 3 leads	SOT323			

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

## 4. Marking

Table 5. Marking codes

in i	
Type number	Marking code <sup>[1]</sup>
PDTC123YE	19
PDTC123YK	31
PDTC123YM	G7
PDTC123YS	TC123Y
PDTC123YT	*AL
PDTC123YU	*19

<sup>[1] \* = -:</sup> made in Hong Kong

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	N	lin	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-		50	V
$V_{CEO}$	collector-emitter voltage	open base	-		50	V
$V_{EBO}$	emitter-base voltage	open collector	-		5	V
$V_{I}$	input voltage					
	positive		-		+12	V
	negative		-		-5	V
Io	output current (DC)		-		100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1$ ms	-		100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$				
	SOT416		<u>[1]</u> _		150	mW
	SOT346		<u>[1]</u> _		250	mW
	SOT883		[2][3]		250	mW
	SOT54		[1] _		500	mW
	SOT23		<u>[1]</u> _		250	mW
	SOT323		[1] _		200	mW
T <sub>stg</sub>	storage temperature		-	65	+150	°C
Tj	junction temperature		-		150	°C
T <sub>amb</sub>	ambient temperature		-	65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

## 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> -	-	833	K/W
	SOT346		<u>[1]</u> -	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> -	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> -	-	625	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Device mounted on an FR4 PCB with 60  $\mu m$  copper strip line, standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

<sup>[3]</sup> Device mounted on an FR4 PCB with 60  $\mu m$  copper strip line, standard footprint.

5 of 11

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

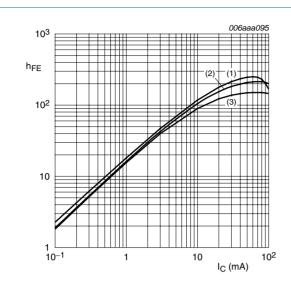
#### **Characteristics 7**.

**Product data sheet** 

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

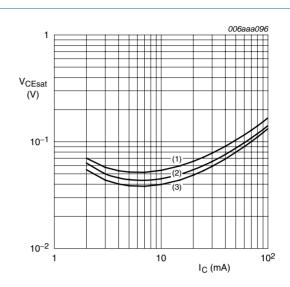
	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	700	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	35	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.75	0.3	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 300 \text{ mV}; I_{C} = 20 \text{ mA}$	2.5	1.15	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	$k\Omega$
R2/R1	bias resistor ratio		3.6	4.5	5.5	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2	pF
-						



$$V_{CE} = 5 V$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2) T<sub>amb</sub> = 25 °C
- (3)  $T_{amb} = -40 \, ^{\circ}C$

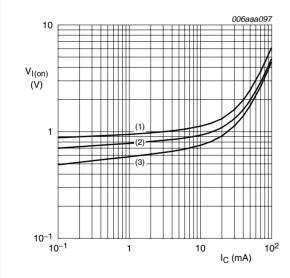
Fig 1. DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

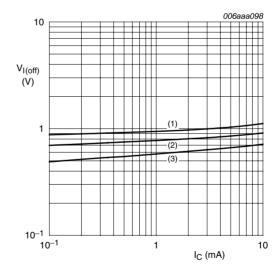
Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values





- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 3. On-state input voltage as a function of collector current; typical values



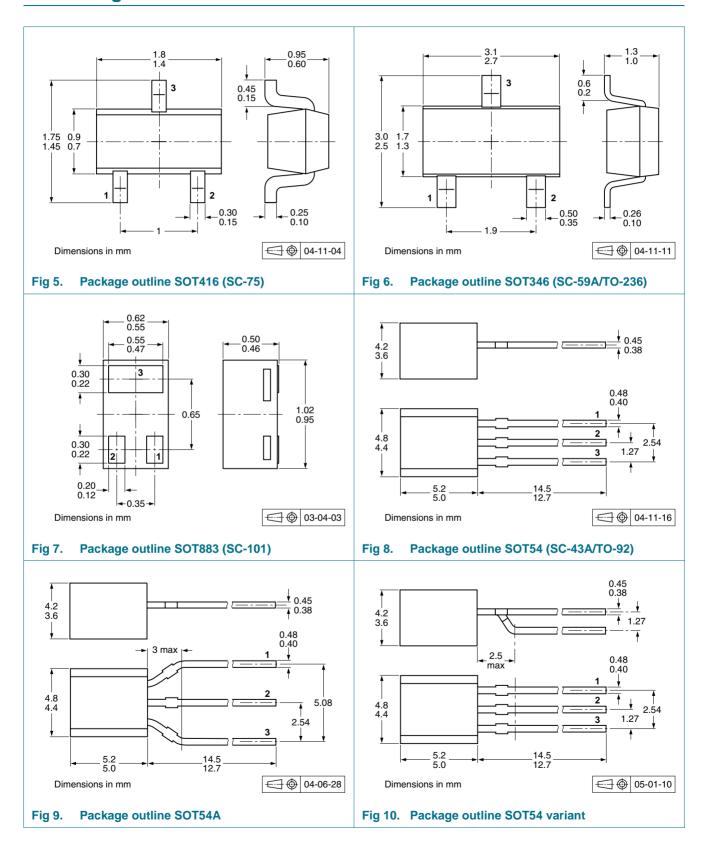
$$V_{CE} = 5 V$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 4. Off-state input voltage as a function of collector current; typical values

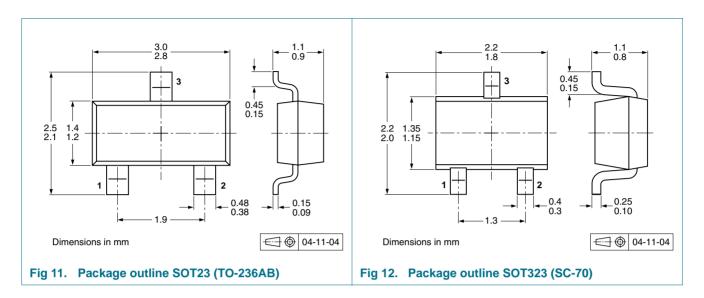
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## 8. Package outline



8 of 11

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 



## **Packing information**

Table 9. **Packing methods** 

**Product data sheet** 

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing (	Packing quantity		
			3000	5000	10000	
PDTC123YE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC123YK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTC123YM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315	
PDTC123YS	SOT54	bulk, straight leads	-	-412	-	
	SOT54A	tape and reel, wide pitch	-	-	-116	
		tape ammopack, wide pitch	-	-	-126	
	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTC123YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	
PDTC123YU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135	

<sup>[1]</sup> For further information and the availability of packing methods, see Section 12.

9 of 11

NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

## 10. Revision history

## Table 10. Revision history

**Product data sheet** 

	•				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTC123Y_SER_4	20091116	Product data sheet	-	PDTC123Y_SER_3	
Modifications:	<ul> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> </ul>				
PDTC123Y_SER_3	20050324	Product data sheet	-	PDTC123YT_2	
PDTC123YT_2	20040510	Objective data sheet	-	PDTC123YT_1	
PDTC123YT_1	20040406	Objective data sheet	-	-	

## 11. Legal information

### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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# PDTC123Y series

## NPN resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

## 13. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 3
4	Marking 3
5	Limiting values 4
6	Thermal characteristics 4
7	Characteristics 5
8	Package outline
9	Packing information 8
10	Revision history9
11	Legal information
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks 10
12	Contact information 10
13	Contents

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